

WHAT IS CLAIMED IS:

1. A method of forming wiring in a semiconductor device, comprising the steps of:

forming a conductive layer on an insulating film formed on a semiconductor substrate;

depositing a nitride film on said conductive layer by a low-pressure chemical vapor deposition method to form a hard mask layer ;

patterning said hard mask layer to form a patterned hard mask;

patterning said conductive layer using the patterned hard mask to form a patterned conductive layer; and

depositing a nitride film by a low-pressure chemical vapor deposition method and then etching a spacer to form a spacer at a sidewall of the patterned conductive layer and the hard mask.

2. The method of claim 1, wherein the process of depositing the nitride film for forming the hard mask and the spacer is performed in a single type chamber having a temperature of 600°C to 800°C and a pressure of 1 Torr to 500 Torr.

3. The method of claim 1, wherein said hard mask is formed in a thickness of 500Å to 3000Å.

4. The method of claim 1, wherein the process of depositing the nitride

CI

~~When~~
A to 10